



# UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE  
United States Patent and Trademark Office  
Address: COMMISSIONER FOR PATENTS  
P.O. Box 1450  
Alexandria, Virginia 22313-1450  
[www.uspto.gov](http://www.uspto.gov)

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/626,365	07/23/2003	Anand Murthy	042390P9490D	1228
7590	06/10/2004			EXAMINER
Stephen M. De Clerk				KANG, DONGHEE
BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP				
Seventh Floor			ART UNIT	PAPER NUMBER
12400 Wilshire Boulevard			2811	
Los Angeles, CA 90025-1026				
				DATE MAILED: 06/10/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

A7

<b>Office Action Summary</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	10/626,365	MURTHY ET AL.	
	<b>Examiner</b>	<b>Art Unit</b>	
	Donghee Kang	2811	

-- The MAILING DATE of this communication appears on the cover sheet with the corresponding address --  
**Period for Reply**

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

**Status**

1) Responsive to communication(s) filed on 23 July 2003.  
 2a) This action is **FINAL**.                    2b) This action is non-final.  
 3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

**Disposition of Claims**

4) Claim(s) 25-38 is/are pending in the application.  
 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.  
 5) Claim(s) \_\_\_\_\_ is/are allowed.  
 6) Claim(s) 25-27 and 35-38 is/are rejected.  
 7) Claim(s) 28-34 is/are objected to.  
 8) Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

**Application Papers**

9) The specification is objected to by the Examiner.  
 10) The drawing(s) filed on 23 July 2003 is/are: a) accepted or b) objected to by the Examiner.  
 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).  
 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).  
 11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

**Priority under 35 U.S.C. § 119**

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
 a) All    b) Some \* c) None of:  
 1. Certified copies of the priority documents have been received.  
 2. Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.  
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

\* See the attached detailed Office action for a list of the certified copies not received.

**Attachment(s)**

1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)	4) <input type="checkbox"/> Interview Summary (PTO-413)
2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No(s)/Mail Date. _____
3) <input checked="" type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date <u>07-23 &amp; 10-10, 03</u> .	5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)
	6) <input type="checkbox"/> Other: _____

## DETAILED ACTION

### ***Priority***

1. This application appears to be a division of Application No. 10/002,465, filed November 01, 2001. A later application for a distinct or independent invention, carved out of a pending application and disclosing and claiming only subject matter disclosed in an earlier or parent application is known as a divisional application or "division." The divisional application should set forth only that portion of the earlier disclosure which is germane to the invention as claimed in the divisional application.

### ***Information Disclosure Statement***

2. Acknowledgment is made of receipt of applicant's Information Disclosure Statement (PTO-1449) filed July 23 & October 10, 2003.

### ***Claim Rejections - 35 USC § 102***

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(a) the invention was known or used by others in this country, or patented or described in a printed publication in this or a foreign country, before the invention thereof by the applicant for a patent.

4. Claims 25-27, 35 & 38 are rejected under 35 U.S.C. 102(a) as being anticipated by Shenoy (US 6,239,472).

Re claim 25, Shenoy teaches a method of forming a transistor comprising (Figs.2A-3A):

Forming a gate dielectric layer (204) on a layer of semiconductor material (200); forming a gate electrode (206) on the gate dielectric layer; implanting dopant into the

Art Unit: 2811

layer of the semiconductor material to form doped tip regions in the layer with a channel between the tip regions (Fig.2B; Col.6, lines 24-35); etching the layer to form source and drain recesses in the layer with the tip regions between the recesses (Fig.2D); and filling the source and drain recesses with a source and a drain respectively (Fig.2E).

Re claim 26, Shenov teaches at least one of the source and the drain is made of a film material which:

- (a) includes a dopant selected from one of a p-dopant and an n-dopant (Col.7, lines 25-30); and
- (b) is formed epitaxially on the semiconductor material (Col.7, lines 10-11).

Re claim 27, Shenov teaches that the source and drain have a depth between 2000 Å and 4000 Å (Col.6, lines 49-55) and are spaced by a width (2500 Å ~ 4500 Å: Col.6, lines 59-67) from one another, a ratio of the depth to the width being at least 0.12.

Re claim 35, Shenov teaches (a) if the dopant of the film material is a p-dopant of the tip regions are p-dopants; and (b) if the dopant of the film material is an n-dopant, the dopant of the tip regions are n-dopants.

Re claim 38, Shenov teaches the gate dielectric layer is formed before the dopants are implanted.

#### ***Claim Rejections - 35 USC § 103***

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

- (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the

Art Unit: 2811

invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

6. Claims 36-37 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shenoy (US 6,239,472).

Shenoy does not explicitly teach the dopant comprises at least  $0.5 \times 10^{20} \text{ cm}^{-3}$ . of the film material and the film material has a resistivity of less than 1.1 mOhm-cm. However, Shenoy teaches that the film material has the dopant concentration that is between about  $1 \times 10^{18} \text{ cm}^{-3}$  and  $1 \times 10^{21} \text{ cm}^{-3}$  (Col.7, lines 25-30).

Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to select the dopant concentration in order to obtain a particular resistivity of the source/drain regions.

See also MPEP 2144.05. In the case where the claimed ranges "overlap or lie inside ranges disclosed by the prior art" a prima facie case of obviousness exists. In re Wertheim, 541 F.2d 257, 191USPQ 90 (CCPA 1976); In re Woodruff, 919 F.2d 1575, 16 USPQ2d 1934 (Fed.Cir. 1990) (The prior art taught carbon monoxide concentrations of "about 1-5%" while the claim was limited to "more than 5%." The court held that "about 1-5%" allowed for concentrations slightly above 5% thus the ranges overlapped.); In re Geisler, 116 F.3d 1465, 1469-71, 43 USPQ2d 1362, 1365-66 (Fed. Cir. 1997) (Claim reciting thickness of a protective layer as falling within a range of "50 to 100 Angstroms" considered prima facie obvious in view of prior art reference teaching that "for suitable protection, the thickness of the protective layer should be not less than about 10 nm [i.e., 100Angstroms]." The court stated that "by stating that suitable protection' is

Art Unit: 2811

provided if the protective layer is about' 100 Angstroms thick, [the prior art reference] directly teaches the use of a thickness within [applicant's] claimed range.").

***Allowable Subject Matter***

7. Claims **28-34** are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

The following is a statement of reasons for the indication of allowable subject matter:

Prior art reference, taken along or in combination, do not teach or render obvious that the semiconductor material has a first lattice with a first spacing and the film material has a second lattice having a second structure which is the same as the first structure, the second lattice having a second spacing which differs from the first spacing.

***Conclusion***

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Donghee Kang whose telephone number is 571-272-1656. The examiner can normally be reached on Monday through Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Eddie C Lee can be reached on 571-272-1732. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 2811

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).



Donghee Kang, Ph.D  
Primary Examiner  
Art Unit 2811

dhk